ABSTRACT

METHOD OF WAFER MARKING FOR MULTI-LAYER METAL PROCESSES

A new method of forming a laser mark without damage to the wafer surface is described. A pad oxide layer is formed on a silicon wafer. A nitride layer is deposited overlying the pad oxide layer. A first trench is laser cut through the nitride layer and the pad oxide layer into the silicon wafer. The trench is etched to a second depth wherein the nitride layer is used as a hard mask and wherein the trench forms an identification mark.

FIGURE 3

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